ABSTRACT

A through hole P of this infrared sensor is formed in a position opposed to an adhesive layer AD. The through hole P, the bottom part thereof and an insulating film Pi formed therein is restrained from being deteriorated and damaged, in order to improve the characteristics of the infrared sensor, since the through hole P and the bottom part thereof are supported by the adhesive layer AD even when a pressure difference is generated between the inside and the outside in the space partitioned by the adhesive layer AD.

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